

Transistors

Low Frequency Transistor (20V, 3A)

2SD2150

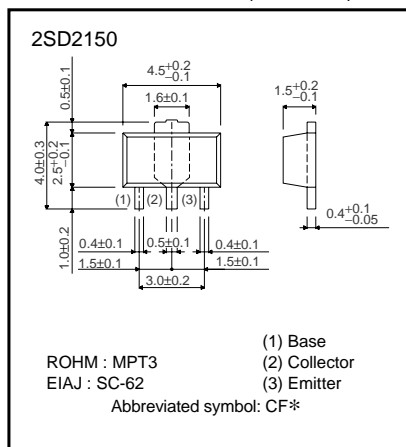
●Features

- 1) Low $V_{CE(sat)}$.
 $V_{CE(sat)} = 0.2V(Typ.)$
 $(I_c / I_B = 2A / 0.1A)$
- 2) Excellent current gain characteristics.
- 3) Complements the 2SB1424.

●Structure

Epitaxial planar type
 NPN silicon transistor

●External dimensions (Unit : mm)



●Absolute maximum ratings ($T_a=25^\circ C$)

| Parameter | Symbol | Limits | Unit |
|-----------------------------|-----------|-------------|--------------|
| Collector-base voltage | V_{CBO} | 40 | V |
| Collector-emitter voltage | V_{CEO} | 20 | V |
| Emitter-base voltage | V_{EBO} | 6 | V |
| Collector current | I_c | 3 | A (DC) |
| | | 5 | A (Pulse) *1 |
| Collector power dissipation | P_C | 0.5 | W |
| | | 2 | W *2 |
| Junction temperature | T_j | 150 | $^\circ C$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ C$ |

*1 Single pulse $P_w=10ms$

*2 Mounted on a 40×40×0.7mm Ceramic substrate.

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●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------------------|----------------------|------|------|------|------|--|
| Collector-base breakdown voltage | BV _{CB0} | 40 | – | – | V | I _C =50μA |
| Collector-emitter breakdown voltage | BV _{CE0} | 20 | – | – | V | I _C =1mA |
| Emitter-base breakdown voltage | BV _{EB0} | 6 | – | – | V | I _E =50μA |
| Collector cutoff current | I _{CB0} | – | – | 0.1 | μA | V _{CB} =30V |
| Emitter cutoff current | I _{EB0} | – | – | 0.1 | μA | V _{EB} =5V |
| Collector-emitter saturation voltage | V _{CE(sat)} | – | 0.2 | 0.5 | V | I _C /I _B =2A/0.1A * |
| DC current transfer ratio | h _{FE} | 120 | – | 560 | – | V _{CE} =2V, I _C =0.1A |
| Transition frequency | f _T | – | 290 | – | MHz | V _{CE} =2V, I _E =–0.5A, f=100MHz |
| Output capacitance | C _{ob} | – | 25 | – | pF | V _{CE} =10V, I _E =0A, f=1MHz |

* Measured using pulse current.

●Packaging specifications and h_{FE}

| Type | h _{FE} | Package | Taping |
|---------|-----------------|------------------------------|--------|
| | | Code | T100 |
| | | Basic ordering unit (pieces) | 1000 |
| 2SD2150 | RS | | ○ |

h_{FE} values are classified as follows :

| Item | R | S |
|-----------------|------------|------------|
| h _{FE} | 180 to 390 | 270 to 560 |

●Electrical characteristic curves

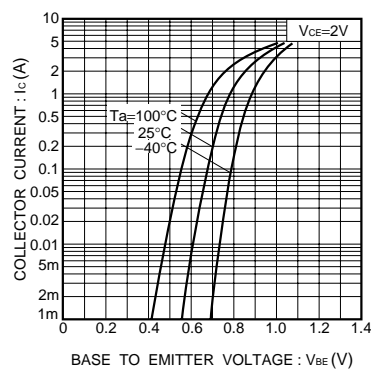


Fig.1 Grounded emitter propagation characteristics

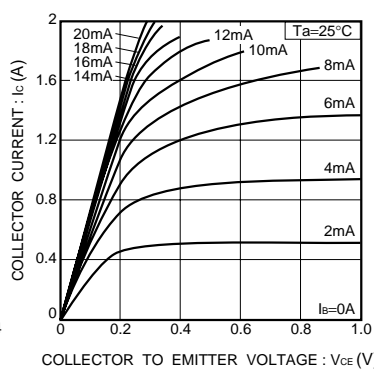


Fig.2 Grounded emitter output characteristics (I)

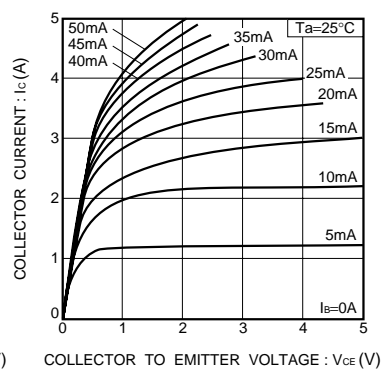


Fig.3 Grounded emitter output characteristics (II)

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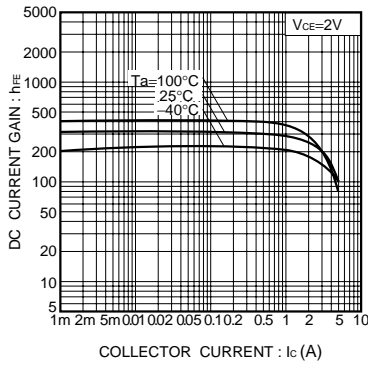


Fig.4 DC current gain vs. collector current

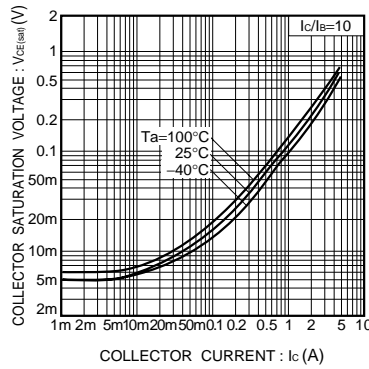


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

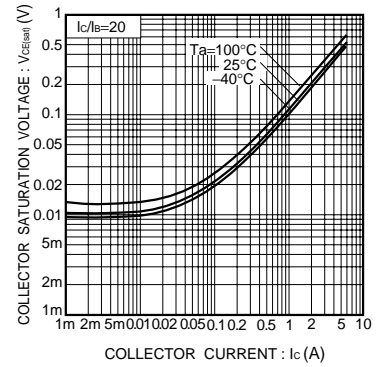


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

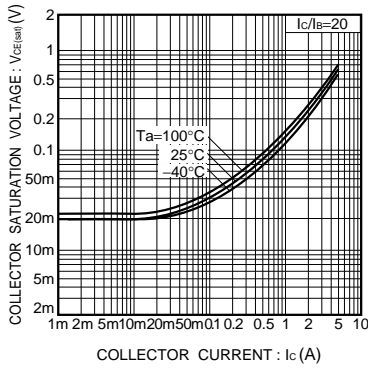


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

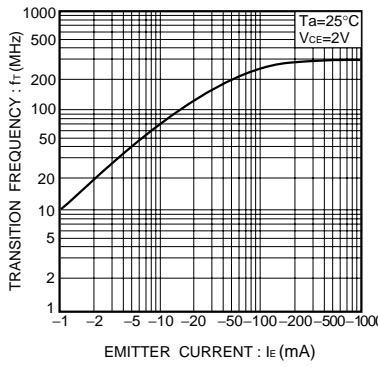


Fig.8 Gain bandwidth product vs. emitter current

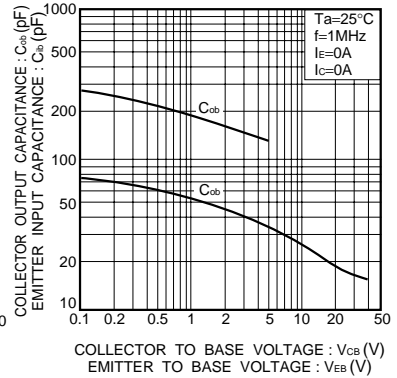


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

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